

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
1	IS&R	L6	5	((("6043157") or ("6087231") or ("6083836") or ("5266519") or ("6475908")).PN.	USPAT; US-PGPUB	2004/07/08 17:06			0
2	IS&R	L7	1	("6750519").PN.	USPAT; US-PGPUB	2004/07/08 17:20			0
3	IS&R	L8	1	("6677652").PN.	USPAT; US-PGPUB	2004/07/08 18:30			0
4	BRS	L9	5473	different\$4 with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:24			0
5	BRS	L10	106203	CMOS or "CMOS"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:33			0
6	BRS	L11	82120	NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:33			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
7	BRS	L12	66079	PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:34			0
8	BRS	L13	133038	10 or (11 and 12)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:34			0
9	BRS	L14	21484	metal adj5 gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:58			0
10	BRS	L15	33191	work\$3 near3 function\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:35			0
11	BRS	L16	10	9 and 13 and 14 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:36			0
12	BRS	L17	7241	conduct\$5 adj oxide\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:47			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
13	BRS	L18	139	metal adj oxide adj gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:47			0
14	BRS	L19	164401 4	ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:48			0
15	BRS	L20	2	conduct\$5 adj oxide adj gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:50			0
16	BRS	L21	35882	(implant\$8 or inject\$4 or dop\$5) near15 (oxygen or O2 or "O2" or "O.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:14			0
17	BRS	L22	59	13 and (14 or 17 or 18 or 20) and 15 and 21	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:55			0
18	BRS	L23	6	22 and 9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:55			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
19	BRS	L24	61576	(metal or 19) near15 gates\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:59			0
20	BRS	L25	3756	(implant\$8 or inject\$4 or dop\$5) with (oxygen or O2 or "O2" or "O.sub.2") with (19 or metal\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:17			0
21	BRS	L26	314	(24 or 20 or 18 or 17) and 25	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:18			0
22	BRS	L27	32	26 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:19			0
23	BRS	L28	10792	(differe\$4 or var\$6 or dissimilar\$4 or divers\$6) with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:27			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
24	BRS	L29	45	28 and (24 or 20 or 18 or 17 or 14) and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:29			0

L Number	Hits	Search Text	DB	Time stamp
6	5	((("6043157") or ("6087231") or ("6083836") or ("5266519") or ("6475908"))).PN.	USPAT; US-PGPUB	2004/07/08 17:06
7	1	("6750519").PN.	USPAT; US-PGPUB	2004/07/08 17:20
8	1	("6677652").PN.	USPAT; US-PGPUB	2004/07/08 18:30
9	5473	differen\$4 with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:24
10	106203	CMOS or "CMOS"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:33
11	82120	NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:33
12	66079	PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:34
13	133038	(CMOS or "CMOS") or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:34
14	21484	metal adj5 gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:58
15	33191	work\$3 near3 function\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:35
16	10	(differen\$4 with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration\$1) and ((CMOS or "CMOS") or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))) and (metal adj5 gate\$1) and (work\$3 near3 function\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:36
17	7241	conduct\$5 adj oxide\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:47
18	139	metal adj oxide adj gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:47
19	1644014	ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:48

20	2	conduct\$5 adj oxide adj gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:50
21	35882	((implant\$8 or inject\$4 or dop\$5) near15 (oxygen or O2 or "O2" or "O.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:14
22	59	((CMOS or "CMOS") or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))) and ((metal adj5 gate\$1) or (conduct\$5 adj oxide\$1) or (metal adj oxide adj gate\$1) or (conduct\$5 adj oxide adj gate\$1)) and (work\$3 near3 function\$1) and ((implant\$8 or inject\$4 or dop\$5) near15 (oxygen or O2 or "O2" or "O.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:55
23	6	((CMOS or "CMOS") or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))) and ((metal adj5 gate\$1) or (conduct\$5 adj oxide\$1) or (metal adj oxide adj gate\$1) or (conduct\$5 adj oxide adj gate\$1)) and (work\$3 near3 function\$1) and ((implant\$8 or inject\$4 or dop\$5) near15 (oxygen or O2 or "O2" or "O.sub.2"))) and (differen\$4 with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:55
24	61576	((metal or (ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re)) near15 gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:59
25	3756	((implant\$8 or inject\$4 or dop\$5) with (oxygen or O2 or "O2" or "O.sub.2") with ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) or metal\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:17
26	314	((((metal or (ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re)) near15 gate\$1) or (conduct\$5 adj oxide adj gate\$1) or (metal adj oxide adj gate\$1) or (conduct\$5 adj oxide\$1)) and ((implant\$8 or inject\$4 or dop\$5) with (oxygen or O2 or "O2" or "O.sub.2") with ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) or metal\$2)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:18
27	32	(((((metal or (ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re)) near15 gate\$1) or (conduct\$5 adj oxide adj gate\$1) or (metal adj oxide adj gate\$1) or (conduct\$5 adj oxide\$1)) and ((implant\$8 or inject\$4 or dop\$5) with (oxygen or O2 or "O2" or "O.sub.2") with ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) or metal\$2)))) and (work\$3 near3 function\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:19
28	10792	((differen\$4 or var\$6 or dissimilar\$4 or divers\$6) with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:27
29	45	((differen\$4 or var\$6 or dissimilar\$4 or divers\$6) with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration\$1) and (((metal or (ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re)) near15 gate\$1) or (conduct\$5 adj oxide adj gate\$1) or (metal adj oxide adj gate\$1) or (conduct\$5 adj oxide\$1) or (metal adj5 gate\$1)) and (work\$3 near3 function\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 19:29
-	94396	CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:32

-	73476	NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:33
-	58888	PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:33
-	18924	metal adj5 gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:34
-	29246	work\$3 near3 function\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:35
-	118169	CMOS or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:53
-	432	(metal adj5 gate\$1) and (work\$3 near3 function\$1) and (CMOS or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/27 15:30
-	95937	CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:53
-	73591	NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:54
-	58981	PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:54
-	119584	(CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:55
-	31830	work\$3 near3 function\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:56
-	6415	conduct\$5 adj oxide\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:47

-	106	metal adj oxide adj gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:47
-	8	((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))) and (work\$3 near3 function\$3) and (metal adj oxide adj gate\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 16:57
-	14	6027961.URPN.	USPAT	2003/09/30 17:06
-	3	6365450.URPN.	USPAT	2003/09/30 17:39
-	4	("5966597" "6033963" "6087208" "6087231").PN.	USPAT	2003/09/30 17:41
-	5	("4605947" "5268590" "5457580" "5600169" "5923999").PN.	USPAT	2003/09/30 17:42
-	1455017	ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:48
-	16402	(ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) and ((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 18:39
-	631	(work\$3 near3 function\$3) and ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) and ((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 18:40
-	102	(ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) with (NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) with (gate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 18:41
-	5	((work\$3 near3 function\$3) and ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) and ((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))))) and ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) with (NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) with (gate\$1 or electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 18:41
-	4742	metal adj gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 18:47
-	29	(metal adj oxide adj gate\$1) and (metal adj gate\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 18:47
-	2	conduct\$5 adj oxide adj gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 18:48
-	5	((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) with (NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) with (gate\$1 or electrode\$1)) and ((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))) and (work\$3 near3 function\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 19:24

-	89	((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) with (NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) with (gate\$1 or electrode\$1)) and ((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 19:24
-	6778	(ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) near15 gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 19:33
-	1225	((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))) and ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) near15 gate\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 19:34
-	75	(work\$3 near3 function\$3) and (((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))) and ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) near15 gate\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 19:34
-	44	(metal adj oxide adj gate\$1) and ((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 20:01